

ABSTRACT OF THE DISCLOSURE

The present invention relates to a plating method and a plating apparatus which can attain embedding of copper into fine interconnection patterns with the use of a plating liquid having
5 high throwing power and leveling properties, and which can make the film thickness of the plated film substantially equal between the interconnection region and the non-interconnection region, thereby facilitating a later CMP processing. A plating method comprising filling a plating liquid containing metal ions and an
10 additive into a plating space formed between a substrate and an anode disposed closely to the substrate so as to face the substrate, and changing the concentration of the additive in the plating liquid filled into the plating space during a plating process.

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